BCR16PM-12L

Triac

Medium Power Use

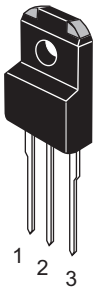
REJ03G0306-0100
Rev.1.00
Aug.20.2004

Features

- $I_{T\,(RMS)}$: 16 A
- V_{DRM} : 600 V
- I_{FGTI}, I_{RGTI}, I_{RGTIII} : 30 mA (20 mA)[Note5]
- Viso : 1500 V
- Insulated Type
- Planar Passivation Type
- UL Recognized : Yellow Card No. E223904
  File No. E80271

Outline

TO-220F





1. T_1 Terminal
2. T_2 Terminal
3. Gate Terminal

Applications

Contactless AC switch, light dimmer, electronic flasher unit, hair drier, control of household equipment such as TV sets, refrigerator, washing machine, electric fan, and other general controlling devices

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak off-state voltage[Note1]	V_{DRM}	600	V
Non-repetitive peak off-state voltage[Note1]	V_{DSM}	720	V

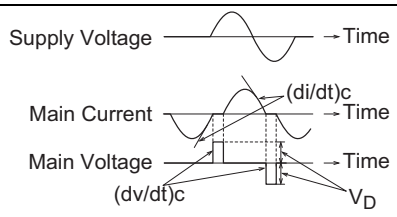
Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T\ (RMS)}$	16	A	Commercial frequency, sine full wave 360° conduction, Tc = 71°C
Surge on-state current	I_{TSM}	160	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I^2t for fusing	I^2t	106.5	A^2s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	5.0	W	
Average gate power dissipation	$P_{G\ (AV)}$	0.5	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I_{GM}	2	A	
Junction temperature	Tj	– 40 to +125	°C	
Storage temperature	Tstg	– 40 to +125	°C	
Mass	—	2.0	g	Typical value
Isolation voltage	Viso	1500	V	Ta = 25°C, AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case

Notes: 1. Gate open.

Electrical Characteristics

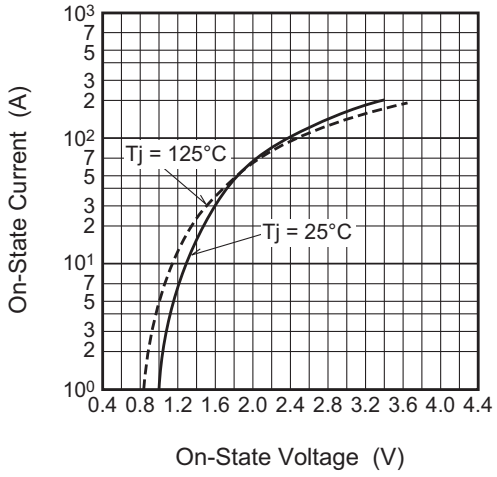
Parameter		Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current		I_{DRM}	—	—	2.0	mA	Tj = 125°C, V_{DRM} applied
On-state voltage		V_{TM}	—	—	1.5	V	Tc = 25°C, I_{TM} = 25 A, Instantaneous measurement
Gate trigger voltage[Note2]	I	V_{FGTI}	—	—	1.5	V	Tj = 25°C, V_D = 6 V, R_L = 6 Ω, R_G = 330 Ω
	II	V_{RGTI}	—	—	1.5	V	
	III	V_{RGTIII}	—	—	1.5	V	
Gate trigger current[Note2]	I	I_{FGTI}	—	—	30[Note5]	mA	Tj = 25°C, V_D = 6 V, R_L = 6 Ω, R_G = 330 Ω
	II	I_{RGTI}	—	—	30[Note5]	mA	
	III	I_{RGTIII}	—	—	30[Note5]	mA	
Gate non-trigger voltage		V_{GD}	0.2	—	—	V	Tj = 125°C, V_D = 1/2 V_{DRM}
Thermal resistance		$R_{th\ (j\text{-}c)}$	—	—	3.0	°C/W	Junction to case[Note3]
Critical-rate of rise of off-state commutating voltage[Note4]		(dv/dt)c	10	—	—	V/µs	Tj = 125°C

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.
3. The contact thermal resistance $R_{th\ (c\text{-}f)}$ in case of greasing is 0.5°C/W.
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.
5. High sensitivity ($I_{GT} \leq$ 20mA) is also available. (I_{GT} item: 1)

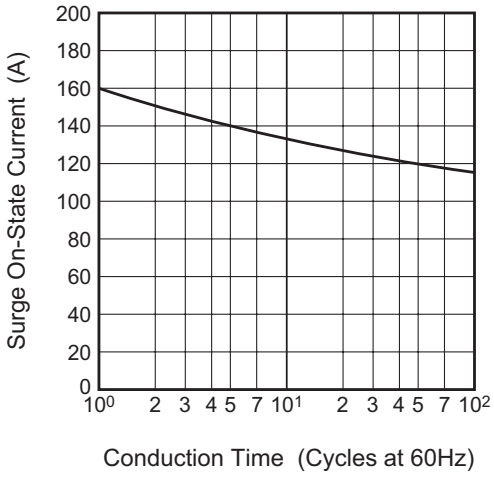
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C 2. Rate of decay of on-state commutating current (di/dt)c = – 8.0 A/ms 3. Peak off-state voltage V_D = 400 V	

Performance Curves

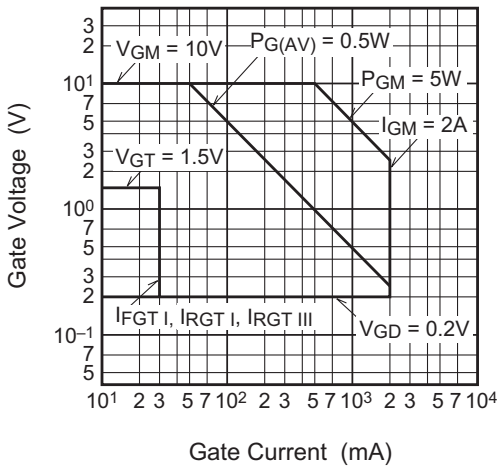
Maximum On-State Characteristics



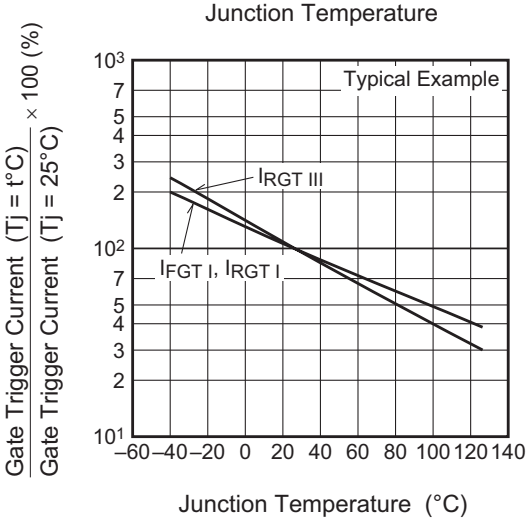
Rated Surge On-State Current



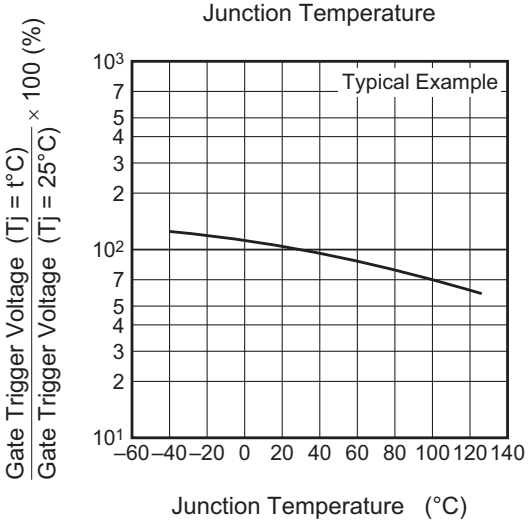
Gate Characteristics (I, II and III)



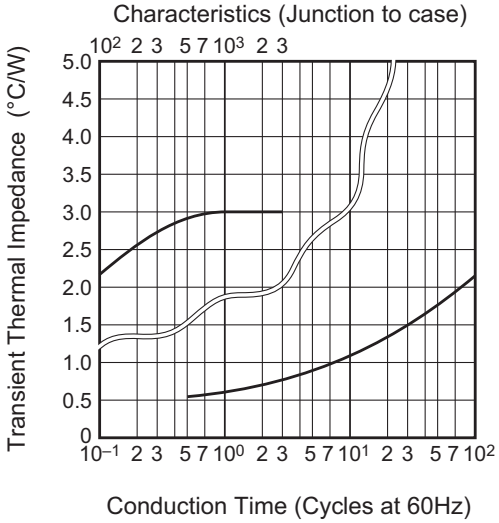
Gate Trigger Current vs. Junction Temperature



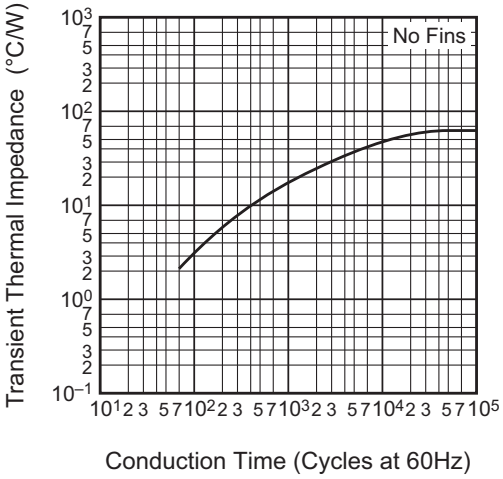
Gate Trigger Voltage vs. Junction Temperature



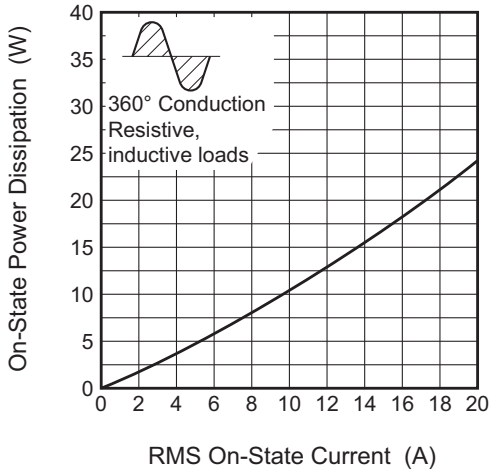
Maximum Transient Thermal Impedance Characteristics (Junction to case)



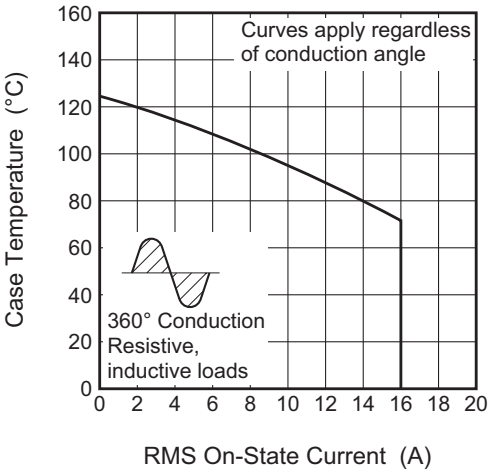
Maximum Transient Thermal Impedance Characteristics (Junction to ambient)



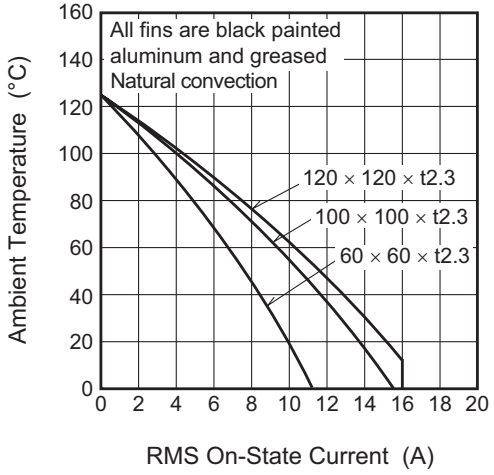
Maximum On-State Power Dissipation



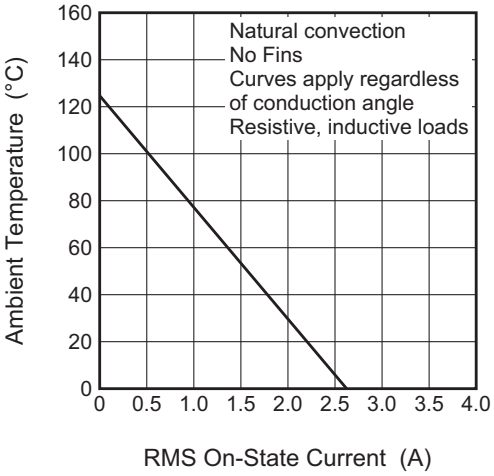
Allowable Case Temperature vs. RMS On-State Current



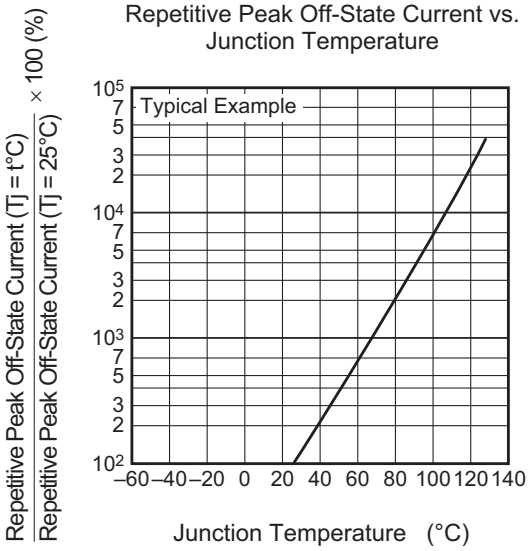
Allowable Ambient Temperature vs. RMS On-State Current



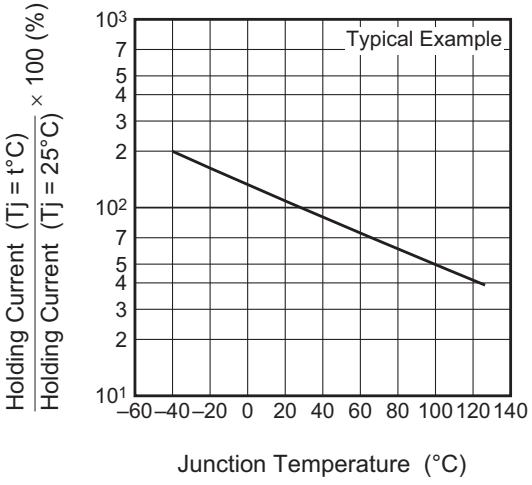
Allowable Ambient Temperature vs. RMS On-State Current



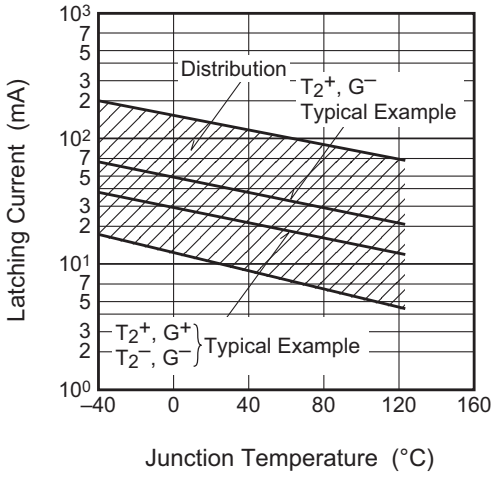
Repetitive Peak Off-State Current vs. Junction Temperature



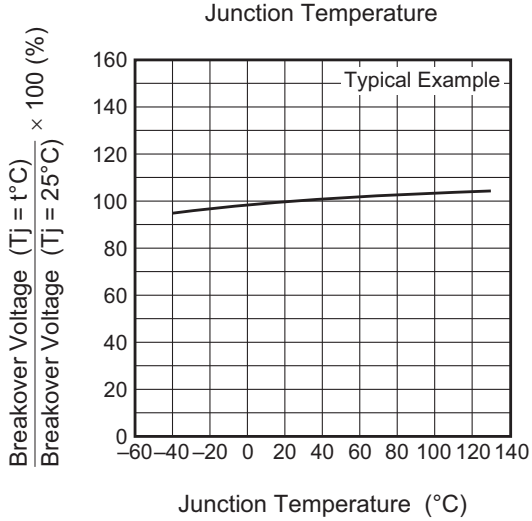
Holding Current vs.
Junction Temperature



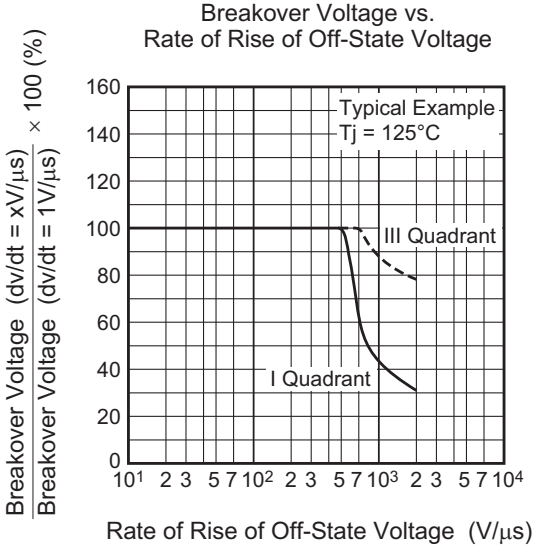
Latching Current vs.
Junction Temperature



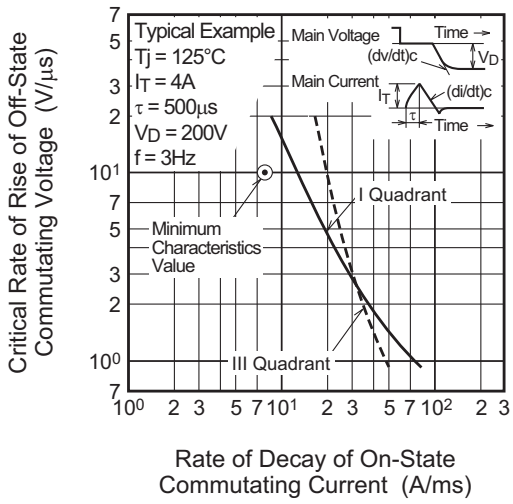
Breakover Voltage vs.
Junction Temperature



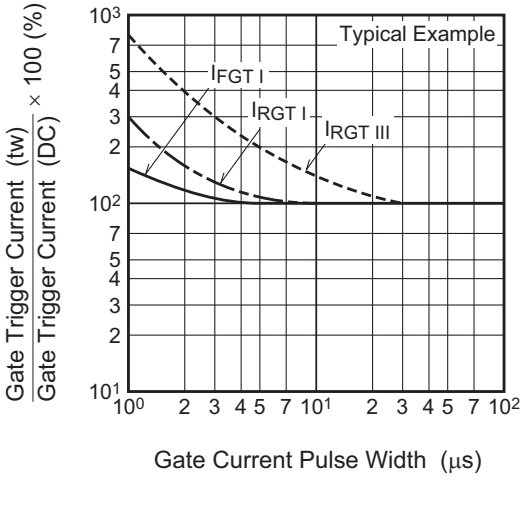
Breakover Voltage vs.
Rate of Rise of Off-State Voltage



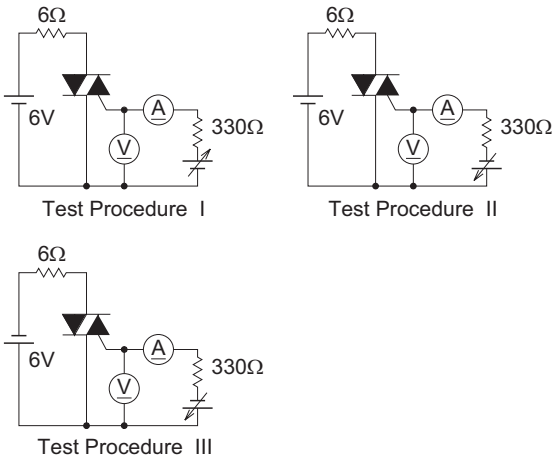
Commutation Characteristics



Gate Trigger Current vs.
Gate Current Pulse Width



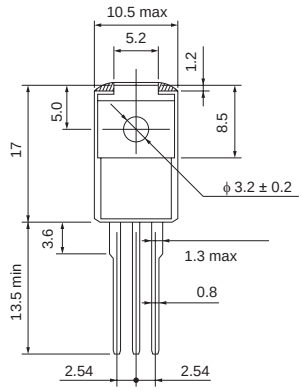
Gate Trigger Characteristics Test Circuits

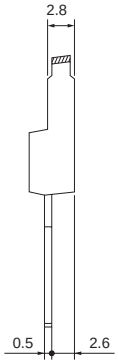


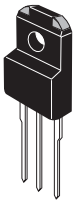
Package Dimensions

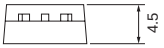
TO-220F

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
Conforms	—	2.0	Cu alloy









Symbol	Dimension in Millimeters		
	Min	Typ	Max
A			
A_1			
A_2			
b			
D			
E			
e			
x			
y			
y_1			
ZD			
ZE			

Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name +A	BCR16PM-12LA
Lead form	Plastic Magazine (Tube)	50	Type name +A – Lead forming code	BCR16PM-12LA-A8

Note : Please confirm the specification about the shipping in detail.

BCR16PM-12L

Triac

Medium Power Use

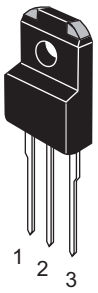
(The product guaranteed maximum junction temperature of 150°C)

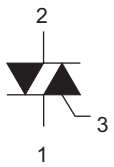
Features

- $I_{T\,(RMS)}$: 16 A
- V_{DRM} : 600 V
- I_{FGTI}, I_{RGTI}, I_{RGTIII} : 30 mA (20 mA)[Note5]
- Viso : 1500 V
- Insulated Type
- Planar Passivation Type

Outline

TO-220F





1. T_1 Terminal
2. T_2 Terminal
3. Gate Terminal

Applications

Contactless AC switch, light dimmer, electronic flasher unit, hair drier, control of household equipment such as TV sets, refrigerator, washing machine, electric fan, and other general controlling devices

Warning

1. Refer to the recommended circuit values around the triac before using.
2. Be sure to exchange the specification before using. Otherwise, general triacs with the maximum junction temperature of 125°C will be supplied.

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak off-state voltage[Note1]	V_{DRM}	600	V
Non-repetitive peak off-state voltage[Note1]	V_{DSM}	720	V

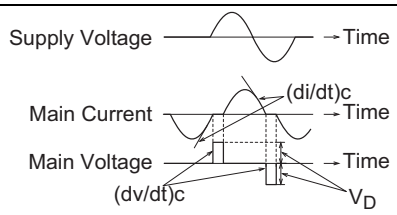
Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T\ (RMS)}$	16	A	Commercial frequency, sine full wave 360° conduction, Tc = 96°C
Surge on-state current	I_{TSM}	160	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I^2t for fusing	I^2t	106.5	A^2s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	5.0	W	
Average gate power dissipation	$P_{G\ (AV)}$	0.5	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I_{GM}	2	A	
Junction temperature	Tj	– 40 to +150	°C	
Storage temperature	Tstg	– 40 to +150	°C	
Mass	—	2.0	g	Typical value
Isolation voltage	Viso	1500	V	Ta = 25°C, AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case

Notes: 1. Gate open.

Electrical Characteristics

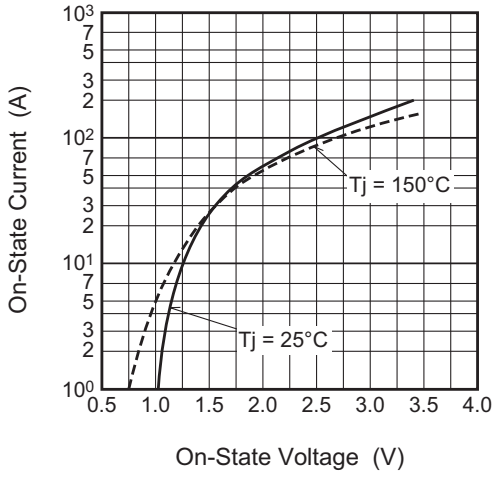
Parameter		Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current		I_{DRM}	—	—	2.0	mA	Tj = 150°C, V_{DRM} applied
On-state voltage		V_{TM}	—	—	1.5	V	Tc = 25°C, I_{TM} = 25 A, Instantaneous measurement
Gate trigger voltage[Note2]	I	V_{FGTI}	—	—	1.5	V	Tj = 25°C, V_D = 6 V, R_L = 6 Ω, R_G = 330 Ω
	II	V_{RGTI}	—	—	1.5	V	
	III	V_{RGTIII}	—	—	1.5	V	
Gate trigger current[Note2]	I	I_{FGTI}	—	—	30[Note5]	mA	Tj = 25°C, V_D = 6 V, R_L = 6 Ω, R_G = 330 Ω
	II	I_{RGTI}	—	—	30[Note5]	mA	
	III	I_{RGTIII}	—	—	30[Note5]	mA	
Gate non-trigger voltage		V_{GD}	0.2/0.1	—	—	V	Tj = 125°C/150°C, V_D = 1/2 V_{DRM}
Thermal resistance		$R_{th\ (j\text{-}c)}$	—	—	3.0	°C/W	Junction to case[Note3]
Critical-rate of rise of off-state commutating voltage[Note4]		(dv/dt)c	10/1	—	—	V/µs	Tj = 125°C/150°C

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.
3. The contact thermal resistance $R_{th\ (c\text{-}f)}$ in case of greasing is 0.5°C/W.
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.
5. High sensitivity ($I_{GT} \leq$ 20 mA) is also available. (I_{GT} item: 1)

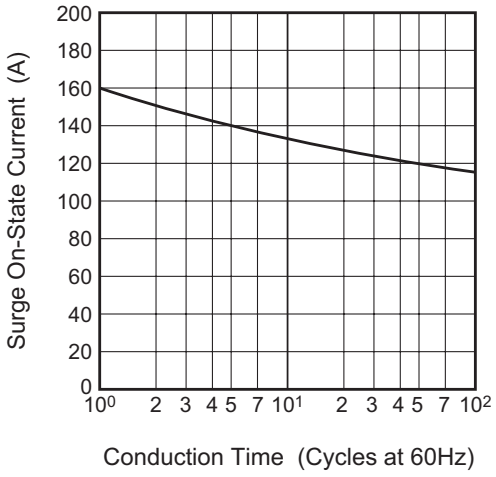
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C/150°C 2. Rate of decay of on-state commutating current (di/dt)c = – 8.0 A/ms 3. Peak off-state voltage V_D = 400 V	

Performance Curves

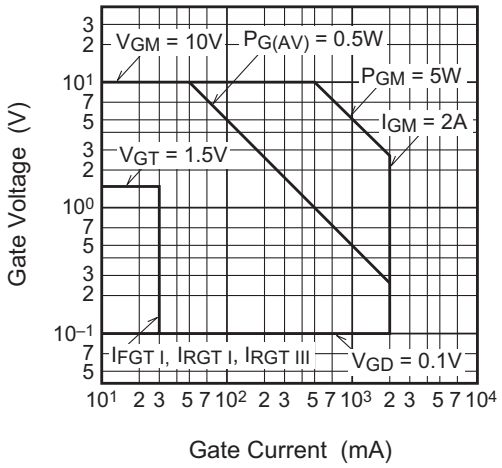
Maximum On-State Characteristics



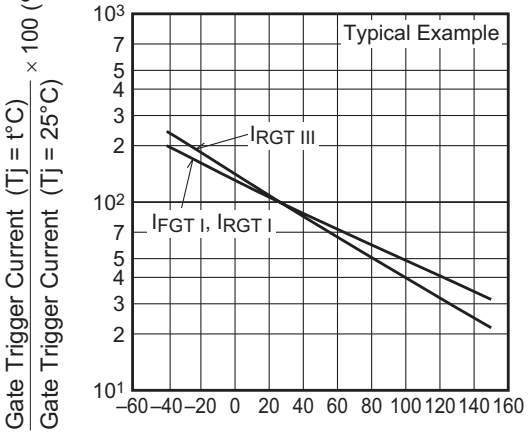
Rated Surge On-State Current



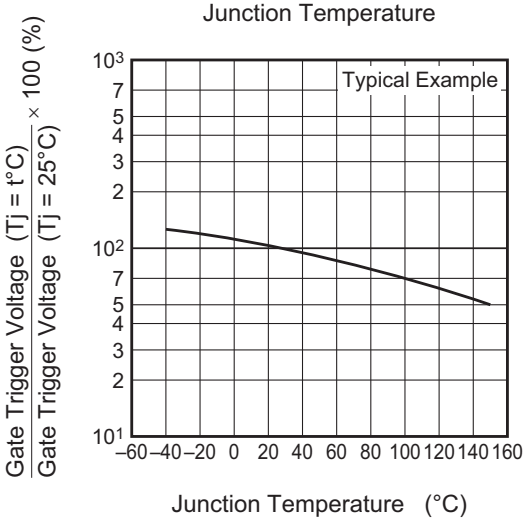
Gate Characteristics (I, II and III)



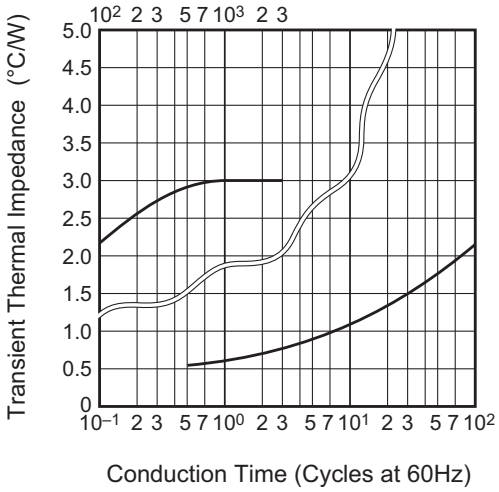
Gate Trigger Current vs. Junction Temperature



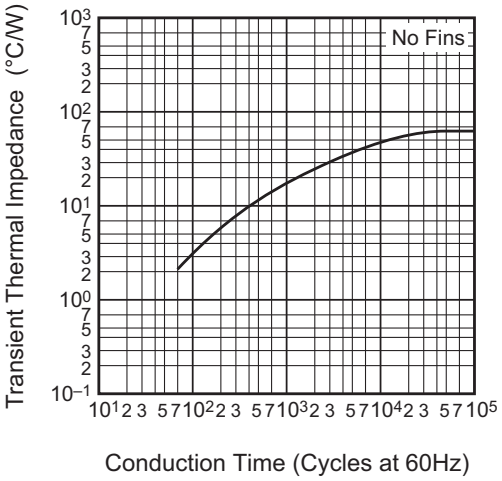
Gate Trigger Voltage vs. Junction Temperature



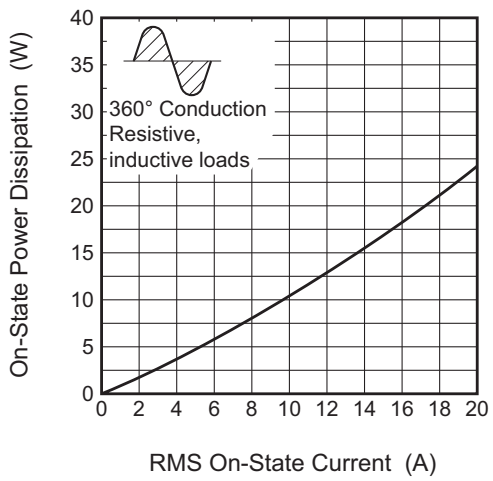
Maximum Transient Thermal Impedance Characteristics (Junction to case)



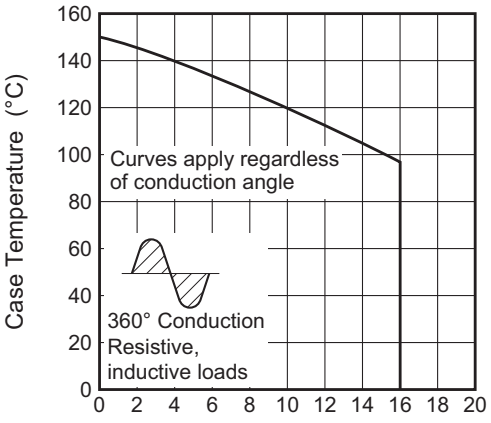
Maximum Transient Thermal Impedance Characteristics (Junction to ambient)



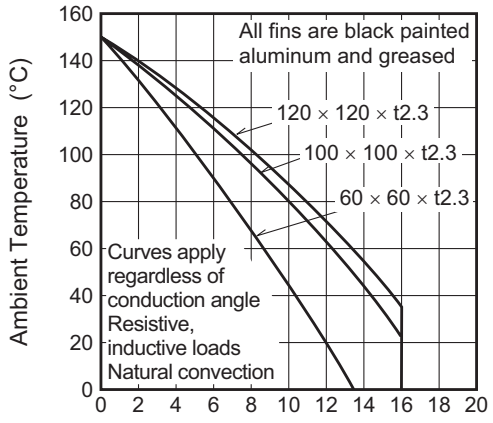
Maximum On-State Power Dissipation



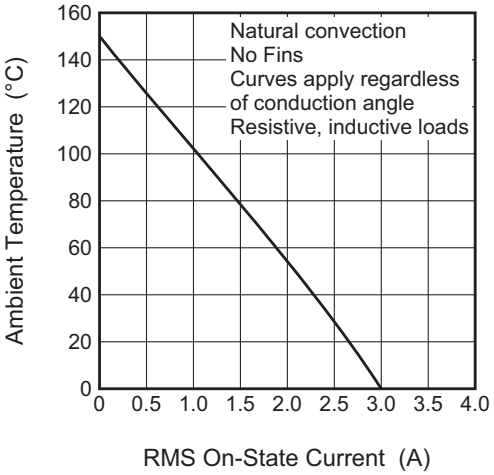
Allowable Case Temperature vs. RMS On-State Current



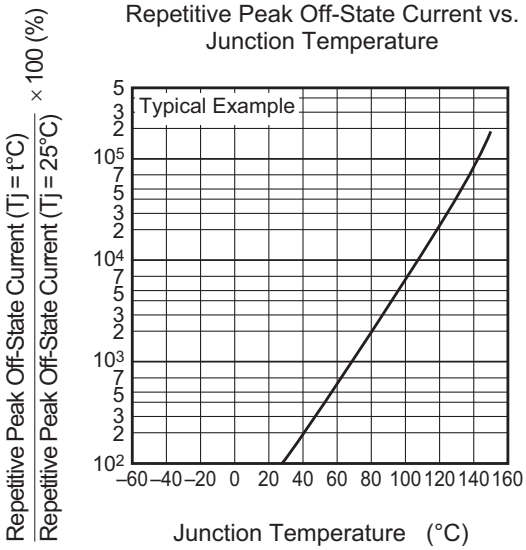
Allowable Ambient Temperature vs. RMS On-State Current



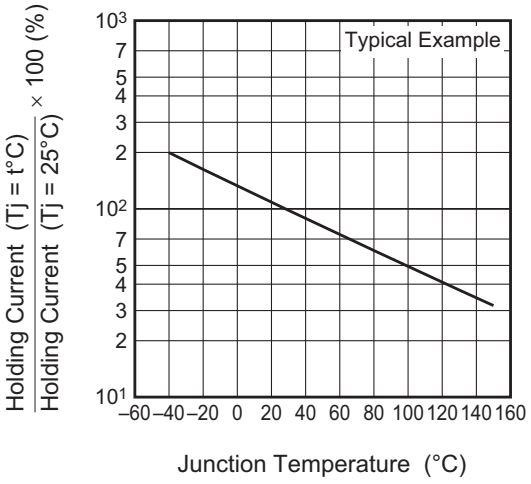
Allowable Ambient Temperature vs. RMS On-State Current



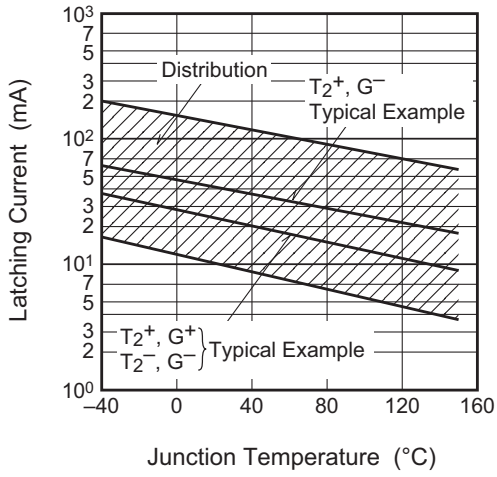
Repetitive Peak Off-State Current vs. Junction Temperature



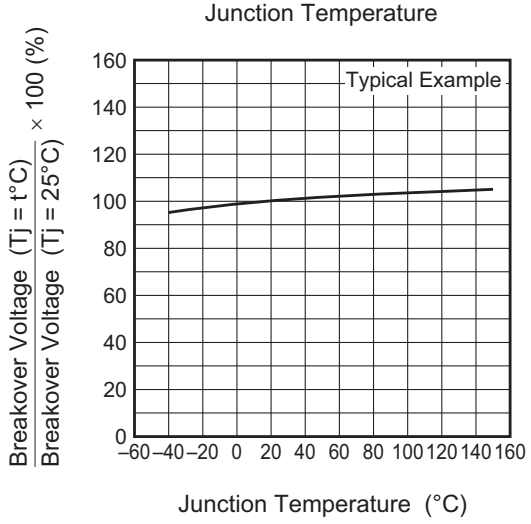
Holding Current vs.
Junction Temperature



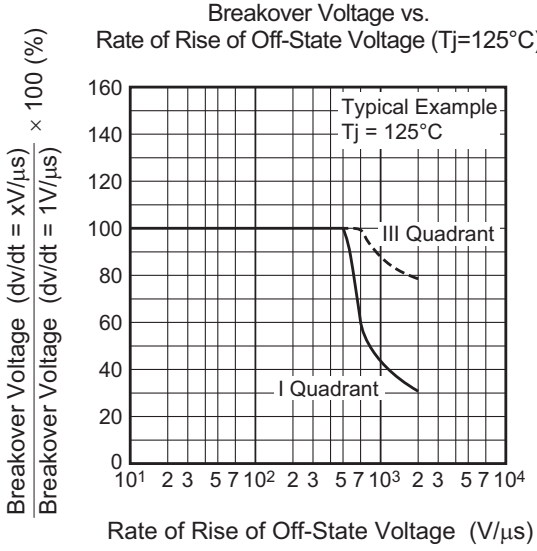
Latching Current vs.
Junction Temperature



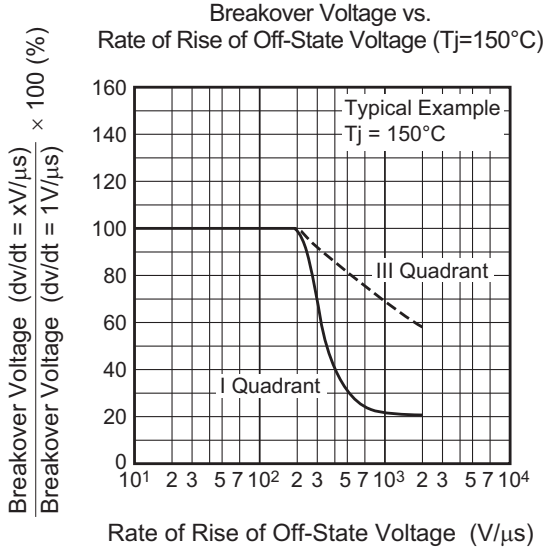
Breakover Voltage vs.
Junction Temperature



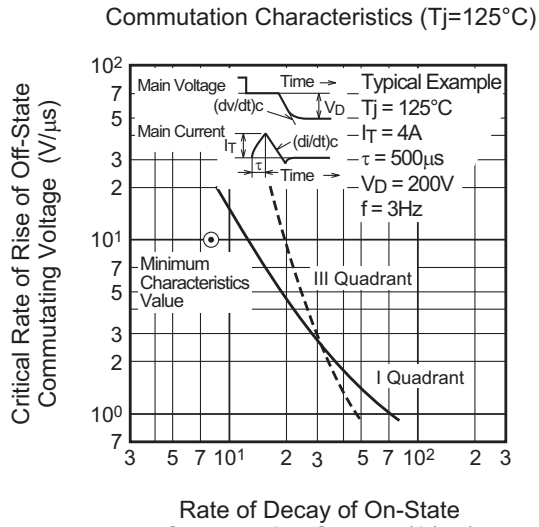
Breakover Voltage vs.
Rate of Rise of Off-State Voltage (Tj=125°C)



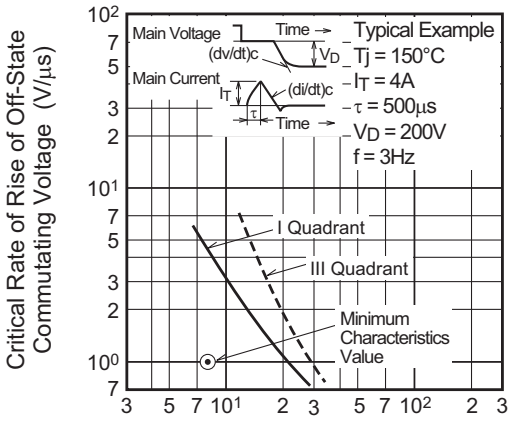
Breakover Voltage vs.
Rate of Rise of Off-State Voltage (Tj=150°C)



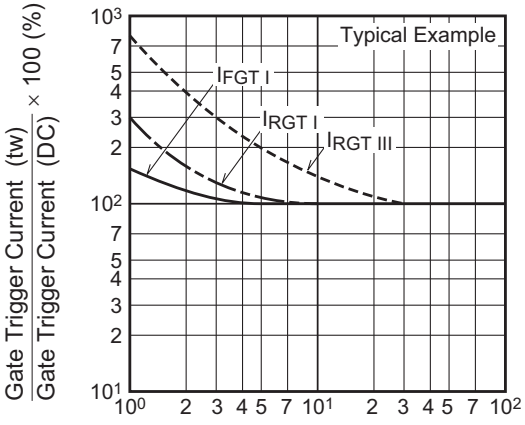
Commutation Characteristics (Tj=125°C)



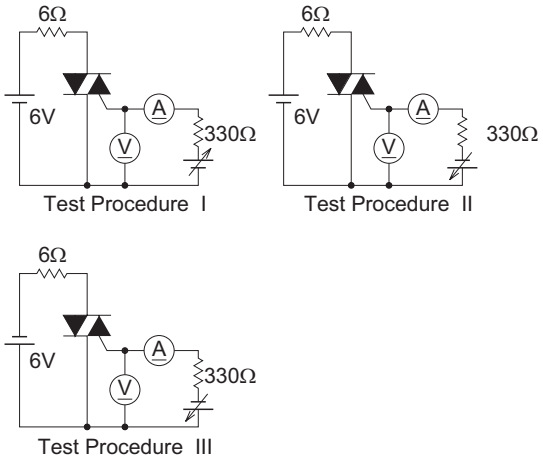
Commutation Characteristics (Tj=150°C)



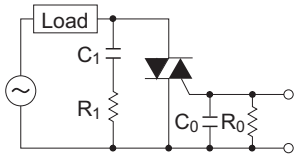
Gate Trigger Current vs. Gate Current Pulse Width



Gate Trigger Characteristics Test Circuits



Recommended Circuit Values Around The Triac

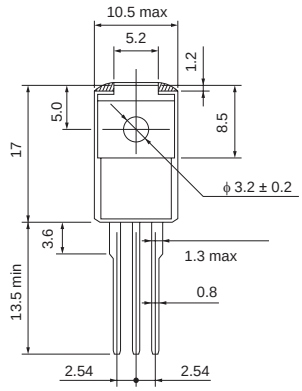


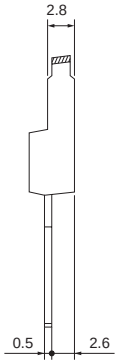
C_1 = 0.1 to 0.47μF C_0 = 0.1μF
R_1 = 47 to 100Ω R_0 = 100Ω

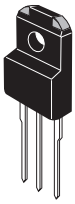
Package Dimensions

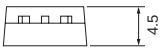
TO-220F

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
Conforms	—	2.0	Cu alloy









Symbol	Dimension in Millimeters		
	Min	Typ	Max
A			
A_1			
A_2			
b			
D			
E			
e			
x			
y			
y_1			
ZD			
ZE			

Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name +B	BCR16PM-12LB
Lead form	Plastic Magazine (Tube)	50	Type name +B – Lead forming code	BCR16PM-12LB-A8

Note : Please confirm the specification about the shipping in detail.

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